

# Charge injection barriers at metal/polyethylene interfaces

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**Abstract** Charge injection barriers at metal/polymer interfaces are affected by many factors, including the physical, chemical, and electronic structure of the metal, the polymer, and the interfacial region. Here, we consider a diverse set of metals (Al, Ag, Au, Pd, and Pt), and a few metal/polyethylene interfacial configurations in an attempt to span situations encountered in real metal/polyethylene systems. Several relevant electronic properties and the charge injection barriers are computed for these cases using density functional theory computations. The calculations reveal important trends and correlations, and identify the favored mechanism of charge transport (as mediated by the charge injection barriers). While satisfactory correspondences of the computations with available measurements are achieved, quantitative discrepancies still remain between the computed and measured injection barriers. These issues may be resolved when more realistic models of the interface, inclusive of its morphological complexities, are utilized.

## Introduction

Charge injection at metal/polymer interfaces in electrical systems such as capacitors and cables is believed to lead to progressive degradation, and ultimately, to the failure of

the embedded polymer dielectric layers [1–5]. This process is governed by the electron and hole injection barriers ( $\phi_e$  and  $\phi_h$ ), at the interface [1], which are, in principle, determined by the appropriate electronic properties of the metal (i.e., its work function), the dielectric (i.e., its band gap and electron affinity), and the interfacial region (i.e., its dipole moment) [1, 2].

Experimentally,  $\phi_e$  and  $\phi_h$  are typically (and directly) estimated by device-level current–voltage characteristics, and the pulsed electroacoustic method which relies on probing the (space) charge density profile across the interface [6]. Among metal/dielectric systems, polymer dielectrics pose enormous challenges to the unambiguous determination of the charge injection barriers. Despite their chemical simplicity, polymers display significant physical complexity—their morphology is composed of crystalline and amorphous regions, and the atomic-level structure at and close to the interface is composed of a diversity of bonding situations [7, 8]. Moreover, polymer dielectrics also contain chemical defects, e.g., occasional C=O (or carbonyl) groups instead of CH<sub>2</sub> units in polyethylene (PE) [9–11]. All these aspects affect the electronic structure across the metal/polymer interface. The measured  $\phi_e$  and  $\phi_h$  naturally include the effects of the complexities alluded to above. Unraveling the specific roles of the various relevant factors in determining  $\phi_e$  and  $\phi_h$  is thus far from trivial.

Determining  $\phi_e$  and  $\phi_h$  for *realistic* metal/polymer interfaces using density functional theory (DFT) calculations is also in a state of infancy [12, 13]. It is worth noting that the theory to determine  $\phi_e$  and  $\phi_h$ , given the interfacial atomic-level structure, is indeed available. In fact, for cases where the interface structure is much less complex than in metal/polymer interfaces (such as GaAs/AlAs [14], HfO<sub>2</sub>/metal [15–19], high-*k* oxide/Si [20–22], etc.),  $\phi_e$ ,  $\phi_h$  as

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well as the effective work function (a related quantity) have been computed with acceptable accuracy.

The essential ingredients necessary to compute  $\phi_e$  and  $\phi_h$  for a metal/insulator system include the work function of the metal ( $\psi_m$ ), the band gap ( $E_g$ ), and the electron affinity ( $E_{ea}$ ) of the insulator, and the interfacial dipole moment-induced vacuum level shift ( $\Delta\varphi$ ). Note that, barring the last quantity (namely,  $\Delta\varphi$ ), the other properties are those of the individual systems that make up the interface. The dipole moment is intimately tied to the interfacial structure and bonding. A lack of knowledge (or an incorrect assumption) of the nature of the interface will lead to errors in the prediction of the dipole moment, and hence  $\phi_e$  and  $\phi_h$ .

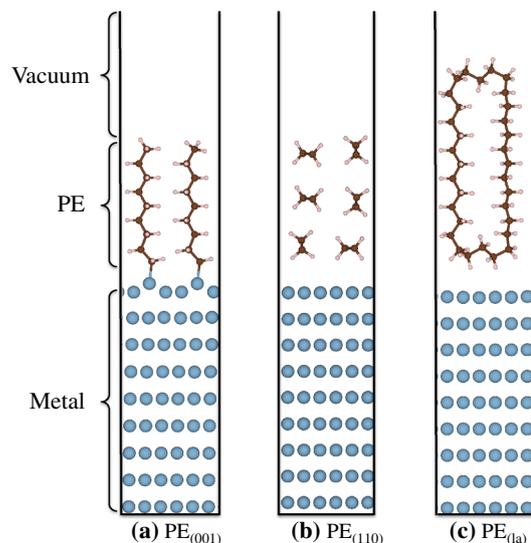
In the present work, we compute  $\phi_e$  and  $\phi_h$  of metal/PE interfaces using DFT, with the metal being Al, Ag, Au, Pd, or Pt (which are conventional choices for practical and model electrodes). This selection of metals also spans a large range of work function values. Three different geometries of contact between PE and the metal were considered, in an attempt to span a few extreme cases of interface configurations. Each of the computed quantities—namely,  $\psi_m$ ,  $E_g$ , and  $E_{ea}$  of PE, and  $\Delta\varphi$  at the metal/PE interface—compares well with available experimental data. Trends in the computed  $\phi_e$  and  $\phi_h$  values, and the (lack of) variation of  $\phi_e$  and  $\phi_h$  with the metal work function are also in favorable agreement with measurements. Nevertheless, the predicted barriers are only in semi-quantitative agreement with the limited available measurements, indicating the need for more realistic models of the metal/PE interface (inclusive of morphological complexity and chemical defects). We hope that such information may be provided by physical and electrical characterization of metal/polymer interfaces in the future.

This paper is organized as follows. “**Models and methods**” section presents the details of the interface models and the computational methodology. In “**Results and discussion**” section, we discuss the calculations of  $\psi_m$ ,  $\Delta\varphi$ ,  $E_{ea}$ , and  $E_g$ , and finally,  $\phi_e$  and  $\phi_h$ . “**Conclusions**” section summarizes the obtained results and proposes some suggestions for future work.

## Models and methods

### Models

Metal/PE interface models were constructed by placing a PE slab on a (111) metal slab (see Fig. 1). The metal slab consisted of nine atomic layers, with the metal being Al, Ag, Au, Pd, or Pt. We considered three different configurations of the PE slab, referred to as PE<sub>(001)</sub>, PE<sub>(110)</sub>, and



**Fig. 1** Geometries of the metal/PE interfaces considered. Metal, carbon, and hydrogen atoms are shown in *blue*, *dark-brown*, and *pink*, respectively. PE chains are normal to the metal surface (**a**, PE<sub>(001)</sub>), parallel to the surface (**b**, PE<sub>(110)</sub>), and are folded next to the surface (**c**, PE<sub>(la)</sub>) (Color figure online)

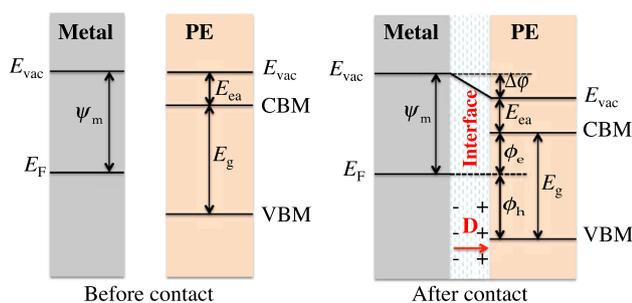
PE<sub>(la)</sub>, wherein the subscript indicates the orientation of the  $-\text{CH}_2-$  chains of crystalline PE. For PE<sub>(001)</sub> and PE<sub>(110)</sub>, the  $-\text{CH}_2-$  chains are normal to and parallel with the metal surface, respectively. PE lamellae, a typical variant of PE whose chains adopt a variety of formats, e.g., curves and fragments [7], are modeled by PE<sub>(la)</sub> in which these chains are folded, approaching the metal surface from different angles. The number of PE layers used in the PE<sub>(001)</sub>, PE<sub>(110)</sub>, and PE<sub>(la)</sub> slabs was 9, 3, and 11, respectively. The in-plane lattice dimensions of the PE slab were slightly strained by a few percent to match with the metal lattice constant at the interface. A vacuum layer of 14 Å was used to suppress the interactions between the system and its periodic images.

### Charge injection barriers

Schematics of the energy diagram of a metal/PE interface are portrayed in Fig. 2. Before contact, the isolated PE and metal slabs share the same vacuum level. When the two materials are contacted, an electric dipole  $\mathbf{D}$  pointing across the interface is created, misaligning the vacuum level of one material with respect to the other by  $\Delta\varphi$ , which can be expressed as [16, 23]

$$\Delta\varphi = -\frac{e|\mathbf{D}|}{\varepsilon_0 A}. \quad (1)$$

Here,  $\varepsilon_0$  is the vacuum permittivity,  $e$  is an electron charge, and  $A$  is the area of the interface.



**Fig. 2** Energy diagram of a metal/PE interface, before (a) and after (b) physical contact, where  $E_F$ ,  $E_{vac}$ , and CBM and VBM are the metal Fermi level, vacuum level, and the conduction band minimum and valence band maximum of PE, respectively. Due to the interfacial dipole moment  $\mathbf{D}$  created after physical contact between the metal and PE, the vacuum levels of the two materials are misaligned by  $\Delta\phi$ . Based on  $\psi_m$ ,  $E_g$ ,  $E_{ea}$ ,  $\phi_e = \psi_m - E_{ea} - \Delta\phi$  and  $\phi_h = E_g - \phi_e$

Assuming that the metal work function  $\psi_m$ , the vacuum level shift  $\Delta\phi$ , the PE electron affinity  $E_{ea}$ , and band gap  $E_g$  are available,  $\phi_e$  is given by

$$\phi_e = \psi_m - E_{ea} - \Delta\phi. \quad (2)$$

$\phi_h$  can be computed as

$$\phi_h = E_g - \phi_e. \quad (3)$$

All the quantities needed to determine  $\phi_e$  and  $\phi_h$ , i.e.,  $\psi_m$ ,  $\Delta\phi$ ,  $E_{ea}$ , and  $E_g$ , can be calculated with DFT, as demonstrated in “Results and discussion” section. We note that apart from  $\Delta\phi$ , the other quantities (namely,  $\psi_m$ ,  $E_{ea}$ , and  $E_g$ ) are properties of the individual materials that make up the interfacial system.

### Calculations details

The properties of the metal, PE, and metal/PE interfaces were calculated using first-principles computations within the framework of DFT [28, 29] as implemented in the Vienna *Ab-initio* Simulation Package (VASP). The generalized gradient approximation Perdew–Burke–Ernzerhof (PBE) [30] functional for the exchange–correlation (XC) energies and a plane wave energy cutoff of 400 eV for the basis set were used. In calculations with bulk metals and crystalline PE, dense Monkhorst-Pack  $\mathbf{k}$ -point meshes of  $14 \times 14 \times 14$  and  $4 \times 4 \times 10$ , respectively, were used to sample their Brillouin zones. For the interface models, the  $\mathbf{k}$ -point mesh was  $4 \times 4 \times 1$ . van der Waals interactions, known to be important in stabilizing polymers like PE [31], were included using the non-local density functional vdW-DF2 [32]. Atomic coordinates were relaxed until atomic forces were smaller than  $0.01 \text{ eV/\AA}$ . The optimized lattice parameters of the bulk metals and PE crystal are listed in Table 1, showing an excellent agreement with experiment data.

**Table 1** Optimized lattice parameters  $a$ ,  $b$ , and  $c$  of the orthorhombic  $Pnma$  PE crystal and  $a$  of the cubic  $Fm\bar{3}m$  Ag, Au, Al, Pd, and Pt crystals, all given in  $\text{\AA}$

System	Lattice constants			Work function		
	This work	Expt.	Ref.	This work	Expt.	Ref.
PE						
$a$	7.00	7.12	[24]			
$b$	4.86	4.85	[24]			
$c$	2.56	2.55	[24]			
Al						
$a$	4.05	4.05	[25]	4.05	4.26	[26]
Ag						
$a$	4.15	4.09	[25]	4.43	4.74	[26]
Au						
$a$	4.16	4.08	[25]	5.21	5.31	[26]
Pd						
$a$	3.94	3.89	[27]	5.30	5.60	[26]
Pt						
$a$	3.97	3.92	[25]	5.70	5.93	[26]

The calculated metal work function is given in eV. For validation, relevant experimental data are also provided

Because  $\phi_e + \phi_h = E_g$ , it is crucial to correctly calculate  $E_g$  in order to determine one of the two barriers, given the other. Moreover, the band edge positions are also required to be properly captured so that quantities such as  $E_{ea}$  can be computed accurately. Calculations at the PBE level of theory systematically underestimate insulator band gap by 30 % or more, and lead to uncertainties in the positions of the band edges [33, 34]. In the case of PE, we obtained a band gap of 6.68 eV with PBE, while the measured band gap of this polymer is 8.80 eV [35]. The state-of-the-art treatment for computing  $E_g$  accurately is the GW method, which is based on many-body perturbation theory [36]. Compared to calculations with PBE, GW calculations are far more expensive but the calculated band gap and band edge positions are significantly more accurate. Here, we calculated the PE band gap as 8.72 eV with  $G_0W_0$ , a version of GW as implemented in VASP. This calculated value agrees well with the true band gap of PE [35], and was used for our calculations of  $E_{ea}$ ,  $\phi_e$ , and  $\phi_h$ .

### Results and discussion

As is evident from the discussion in “Charge injection barriers” section, and Eqs. (2) and (3), computation of the charge injection barrier requires a knowledge of the  $\psi_m$ ,  $E_{ea}$ ,  $E_g$ , and  $\Delta\phi$  for the appropriate systems considered here. Below, we present our results for each of these

quantities (with the exception of  $E_g$ , which was discussed above), and use them to evaluate the charge injection barriers for the metal/PE interfaces.

### The metal work function $\psi_m$

The energy needed to remove an electron from a metal, or the work function  $\psi_m$ , can be calculated as the difference between the metal Fermi level and the metal vacuum level, as shown in Fig. 2. The standard method which has widely been used [15, 37] to calculate  $\psi_m$ , referred to as the “bulk plus band lineup” method [14, 38], involves several steps. First, the energy difference between the average effective potential (experienced by the electrons) and the Fermi energy of the bulk metal system is calculated. Then, calculations for a metal slab with appropriate orientation are performed, determining the average effective potential deep inside the metal slab (i.e., sufficiently far from the surface), as well as the position of the vacuum level. Finally, the energy difference obtained in the first step is used to place the Fermi level with respect to the vacuum level. We show in Table 1 the work function calculated for Al, Ag, Au, Pd, and Pt. Calculated results are within 5 % of the experimentally measured data, indicating that our DFT-based computational scheme is reasonable for determining  $\psi_m$ .

### The PE electron affinity $E_{ea}$

The electron affinity  $E_{ea}$  needed in Eq. (2) for PE is the energy difference between the vacuum level and the conduction band minimum (CBM) of PE. To determine CBM with respect to the vacuum level, the “bulk plus band lineup” procedure described above was used. The electron affinities of the  $PE_{(110)}$ ,  $PE_{(1a)}$ , and  $PE_{(001)}$  slabs (with the band edges of bulk PE calculated with  $G_0W_0$  method) are found to be  $-1.33$  eV,  $-1.23$  eV, and  $-1.16$  eV, respectively. These results agree well with the experimentally measured  $E_{ea}$  that ranges between  $-1.20$  eV and  $0$  eV [35].

### The metal/PE dipole-induced vacuum level shift $\Delta\phi$

Interfacial effects like charge transfer are ubiquitous in heterostructures, leading to the *interface-originated* vacuum level shift  $\Delta\phi$  (see Fig. 2). Starting from the DFT charge density, the electric dipole  $\mathbf{D}$  appearing in Eq. (1) was determined by integrating the elementary dipole moment over the whole total volume of the system. Calculated results for the dipole-induced  $\Delta\phi$  are shown in Table 2. We note that only the  $\Delta\phi$  of Al/ $PE_{(001)}$  takes a positive value, compared with other metal/ $PE_{(001)}$  interfaces. This is because the vacuum energy shift is originated

**Table 2** Calculated vacuum level shift  $\Delta\phi$  of the metal/PE interfaces, given in eV

System	$PE_{(001)}$	$PE_{(1a)}$	$PE_{(110)}$	Expt.
Al-PE	0.29	-0.19	-0.20	-0.30
Ag-PE	-0.20	-0.56	-0.59	-0.50
Au-PE	-1.18	-0.48	-0.58	-0.70
Pd-PE	-1.26	-0.43	-0.72	N/A
Pt-PE	-1.45	-0.59	-0.61	N/A

Experimental data is taken from Ref. [39] for the metal/TTC interface, which is similar to the metal/ $PE_{(110)}$  interface. See text for further details.

from the charge transfer process which is primarily mediated by the metal-carbon bonds formed at the interface. While Al may donate electrons (from the  $3s$  and  $3p$  shells), the other transition metals prefer to gain more electrons for closing their  $d$  shell. This difference leads to charge transfer, and ultimately, vacuum energy shifts, in opposite directions. To the best of our knowledge, similar data for metal/PE interfaces are unavailable. Therefore, for validation purposes, our results were compared with  $\Delta\phi$  measured for the interfaces between tetratetracontane [ $TTC-nCH_3(CH_2)_{42}CH_3$ ] and Al, Ag, and Au [39, 40]. A comparison between the measured metal/TTC and the modeled metal/ $PE_{(110)}$  interfaces is justified because their structures are somewhat similar, i.e., the TTC molecules was found to lie parallel to the metal surface [40]. Indeed, the calculated and measured  $\Delta\phi$  are consistent, suggesting that the results of our calculation methodology for  $\Delta\phi$  at the metal/PE interfaces are appropriate for estimating the charge injection barriers using Eqs. (2) and (3). Nevertheless, we note that the interfacial structure of real metal/PE interfaces may be more complex than the models used here.

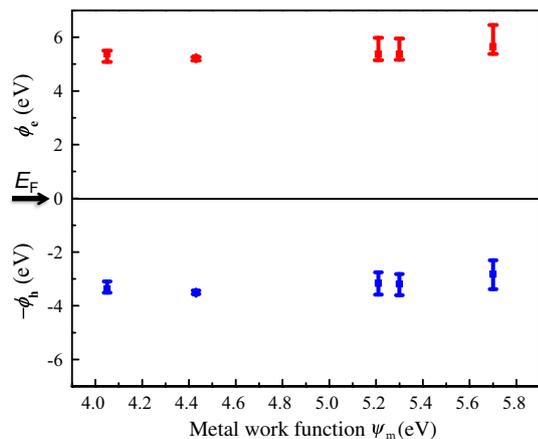
### Electron and hole injection barriers ( $\phi_e$ and $\phi_h$ ) at metal/PE interface

Given the  $\psi_m$ ,  $E_{ea}$ ,  $E_g$ , and  $\Delta\phi$  calculated by DFT,  $\phi_e$  and  $\phi_h$  were determined. The obtained results are shown in Table 3. For ease of visualization, these results are also plotted in Fig. 3. For each choice of metal, both  $\phi_e$  and  $\phi_h$  are shown. The error bars in Fig. 3 represent the spread in the values due to the choice of the interface geometry.

Several observations can be made based on the results captured in Fig. 3. First, it is evident that the charge injection barriers do not follow a clear relationship with the metal work function. For instance, although Al and Pt are, respectively, the metals with the lowest and highest work function values, they do not necessarily lead to the lowest

**Table 3** The computed  $\phi_e$  and  $\phi_h$  of the metal/PE interfaces with  $E_g^{C_{60}W_0}$ , given in eV

System	$\phi_e$			$\phi_h$		
	PE <sub>(110)</sub>	PE <sub>(1a)</sub>	PE <sub>(001)</sub>	PE <sub>(110)</sub>	PE <sub>(1a)</sub>	PE <sub>(001)</sub>
Al/PE	5.39	5.08	5.50	3.33	3.64	3.22
Ag/PE	5.20	5.13	5.26	3.52	3.59	3.46
Au/PE	5.98	5.91	5.19	2.74	2.81	3.53
Pd/PE	5.95	5.82	5.20	2.77	2.90	3.52
Pt/PE	6.46	6.35	5.40	2.26	2.37	3.32

**Fig. 3**  $\phi_e$  and  $\phi_h$  (denoted by red and blue colors, respectively) of the metal/PE interfaces versus  $\psi_m$ . The Fermi energy ( $E_F$ ) of all metal is set as 0. The error bars represent the spread in the barrier height values arising from the choice of the interface geometries (based on the data contained in Table 3) (Color figure online)

and highest charge injection barriers. This aspect is indeed consistent with previous measurements [5], and understandable, because the injection barriers are determined by the combined effects of the metal work function and the vacuum level shift due to the interface dipole moment. Furthermore, for a given metal/PE system, the barriers can be significantly modulated by the details of the interface geometry, as captured by the error bars in Fig. 3, which further diminish the variations in the barriers between different metal/PE systems. These observations allow us to appreciate the important role played by the interface; this can potentially outweigh the effects of the metal work function.

Second, the computed  $\phi_h$  and  $\phi_e$  are, respectively, in the 2.26–3.64 eV and 5.08–6.46 eV ranges. The  $\phi_h$  is thus consistently smaller than  $\phi_e$ , indicating that in the cases considered here, hole conduction will dominate. This phenomenon was previously anticipated via the measurements of the net charge density accumulated in Ag/PE films [5], suggesting that the positive charge injection was more favored under high electric field.

Finally, the predicted barriers are only in semi-quantitative agreement with the limited available measurements.

Current–voltage measurements for Al/PE systems imply a barrier height of 2.14 eV [41] which is in reasonable agreement with the predicted  $\phi_h$  value for the same system. However, more recent measurements for a variety of metal electrodes indicate the charge injection barriers of about 1 eV [2]. The rather partially satisfactory correspondence between computations and measurements for the charge injection barriers is indicative of the possible difference between the interface model simulated and the real complex situation. In other words, more accurate charge injection barriers can only be predicted when more realistic models of the metal/PE interface, incorporating complex morphological details, appropriate atomic binding modes and chemical defects, are captured in the computations.

## Conclusions

An attempt has been made to understand the role of various electronic, physical, and chemical factors in controlling the charge (electron or hole) injection barriers at metal/polymer interfaces, via density functional theory calculations. A variety of metals, including Al, Ag, Au, Pd, and Pt, and a few metal/PE interface models were considered. Computing the charge injection barrier requires the following ingredients: the metal work function, the PE band gap and electron affinity, and the vacuum level shift induced by the interface dipole moment. Of these, the vacuum level shift is intimately controlled by the interfacial structure and bonding, while all the other properties are those of the individual systems that make up the interface.

The present investigation has led to important trends concerning the charge injection barrier. We find that the injection barrier is not a strong function of the metal work function, but is rather determined by the combined effect of the metal work function and the vacuum shift due to the interfacial dipole (which, in turn, is determined by the details of the structure and bonding at the interface). Al, with the lowest work function (of the metals considered here), does not necessarily lead to the smallest barrier, nor does Pt, with a highest work function, display the largest barrier. Moreover, the calculated hole injection barriers are considerably smaller than the electron injection barriers of the same interface, implying that in these interfaces, the hole injection process is dominant. All of these trends, as well as the computed properties of each material, are consistent with the experiments. With respect to the actual values of the charge injection barriers themselves, the computed quantities are overestimated with respect to the available estimates from current–voltage measurements. These discrepancies suggest that more realistic metal/PE interface models, inclusive of the morphological complexity and chemical defects known to be present at

interfaces, should be considered in the computations. It is hoped that such critical information will be provided by detailed physical and electrical characterization of metal/polymer interfaces in the future.

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#### Compliance with ethical standards

**Conflict of interest** The authors declare that they have no conflict of interest.

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